VCSEL Radiation Results with 20 MeV neutrons

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23.06.06 Optoelectronic Working Group Meeting

5 year SLHC fluences in 1MeV neutrons

Challenging radiation environment!!

with a safety factor of 2 1.0E+18 ----- Si **MeV neutron Fluence** - GaAs 1.0E+17 [n/cm^2] 1.0E+16 1.0E+15 **~** 1.0E+14 20 40 60 0 Radius [cm]

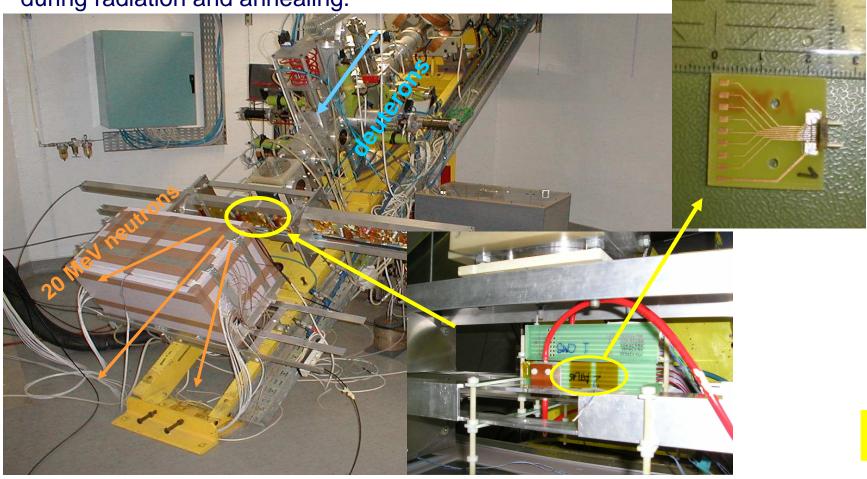
5 years SLHC @ 10^35 cm-2 sec-1

Estimation based on IM. Gregor, Optical Links for ATLAS Pixel Detector, Thesis, WUB DIS 2001 - 03, 2001, Wuppertal

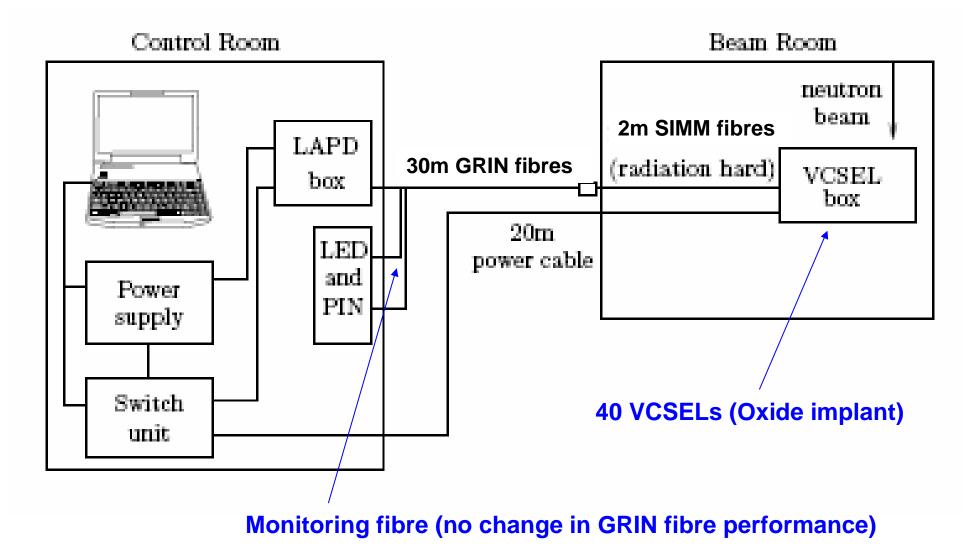
Cyclotron at UCL in Belgium – 20 MeV Neutrons

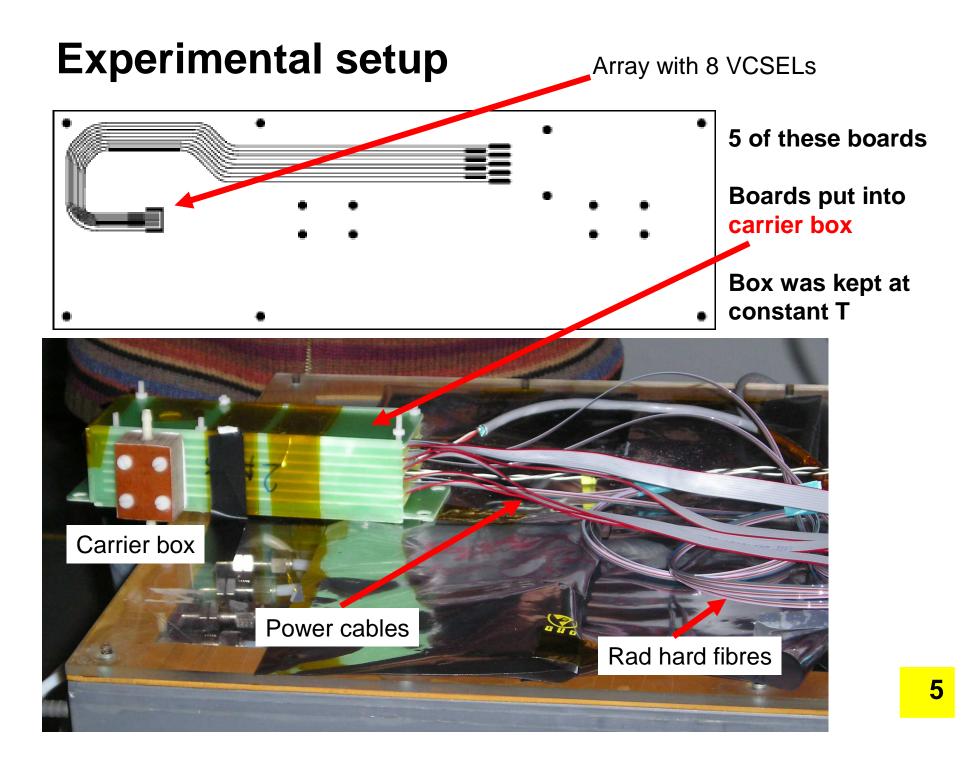
1st test in collaboration with CMS March 06: Great success!!

VCSELs irradiated up to ~10¹⁶ n(1MeV/cm²) and annealed for 2 weeks @ 10mA and 1.5 weeks @ 15mA. Devices were monitored during radiation and annealing.

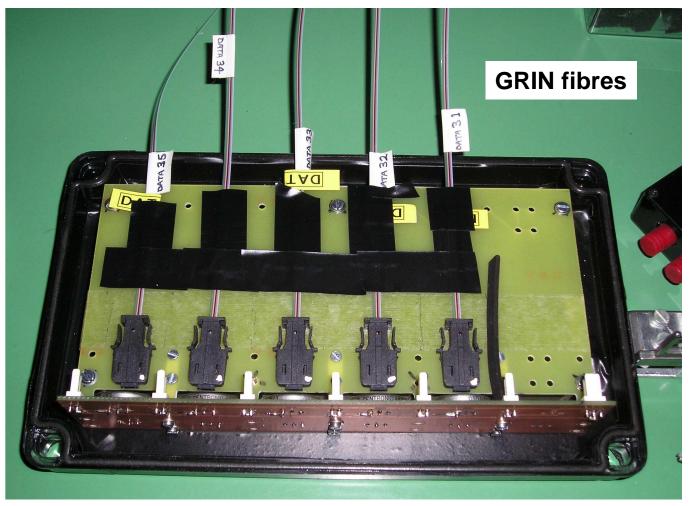


Experimental Setup





Experimetal Setup LAPD Box (open)



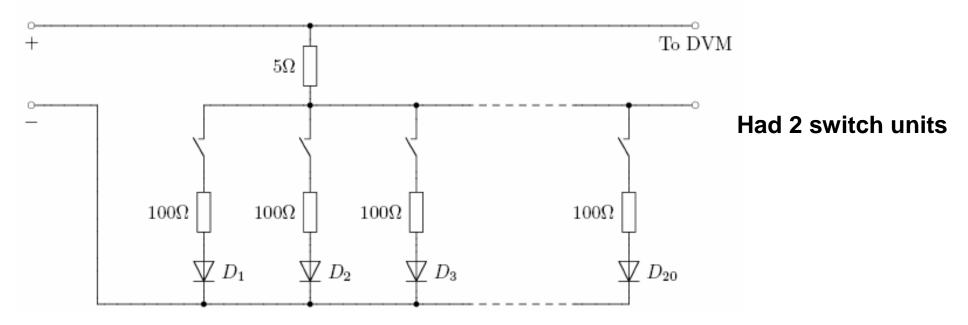
Not shown in picture: Each LAPD was separated by light tight walls from each other.

23.06.06

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Experimental Setup

Circuit of switch unit

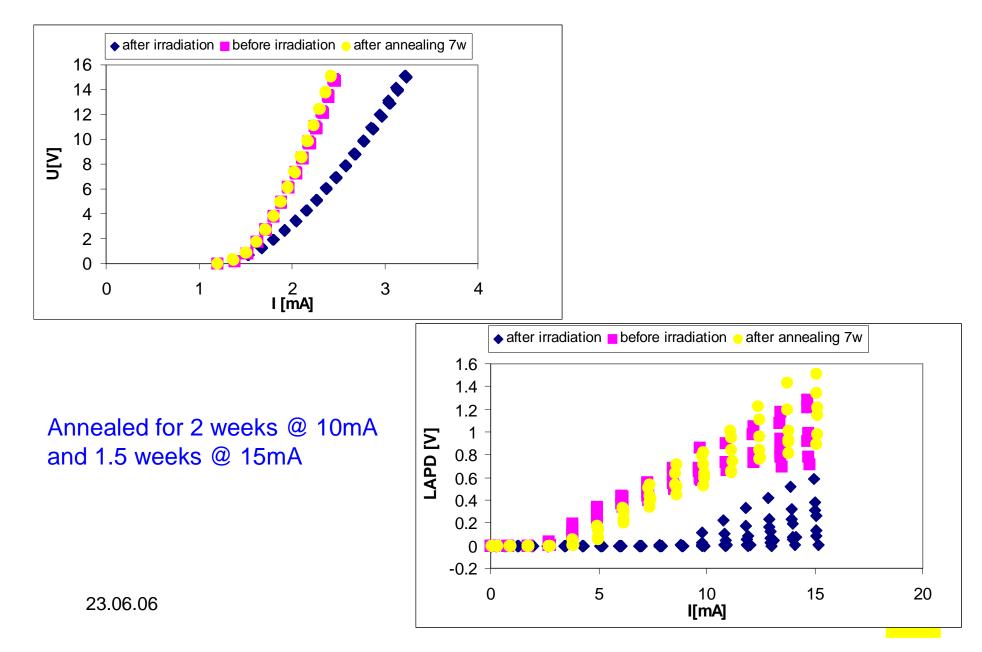


•30 VCSELs were biased in parallel during radiation.
•10 VCSELs were not biased during radiation.
•After 20min biasing L-I-V of each VCSEL was taken.
•T was monitored and was kept at constant level.

Beam Stability and Temperature 20 250 18 ٠ 200 16 14 150 12 Current [muA] 10 beam 100 integrated current 8 6 50 2 0 0 00:00:00 04:48:00 07:12:00 09:36:00 12:00:00 19:12:00 00:00:00 02:24:00 14:24:00 16:48:00 21:36:00 -2 -50 time - VCSEL box --- Controll Room 24 **Biasing VCSELs** ZJ T [C] 22 21 20 04:48:00 09:36:00 14:24:00 00:00:00 19:12:00 23.06.06 Absolute T has an offset of ca. 4 C

t [h]

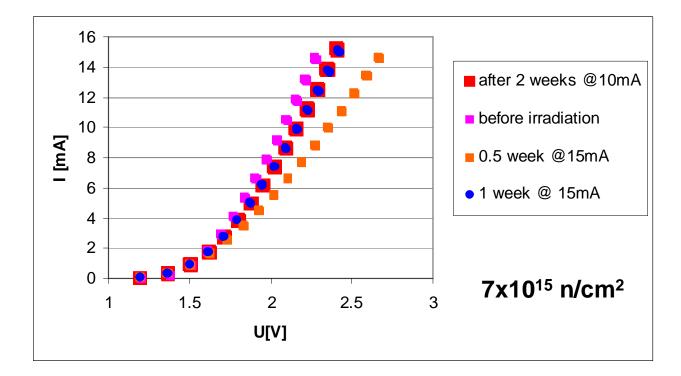
IV and LI Curves for VCSEL array @ 8x10¹⁵ n/cm²



IV Curve developments during annealing

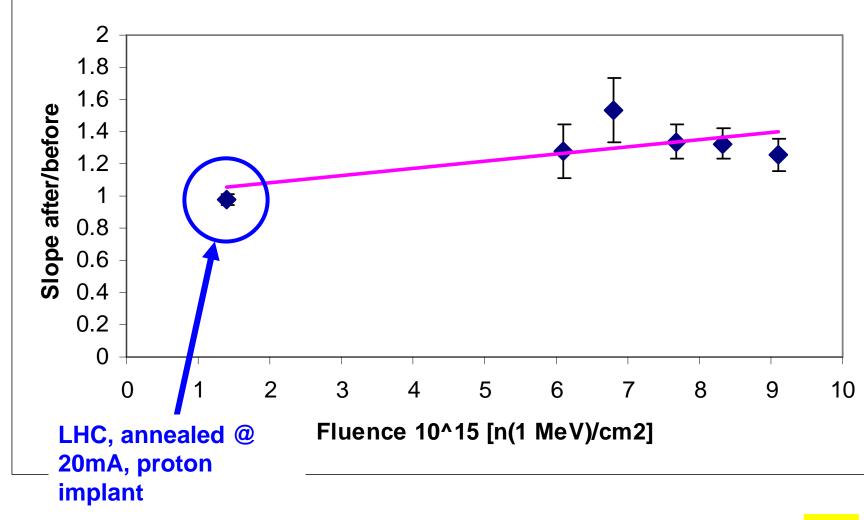
Following is observed during annealing for 3 VCSEL arrays:

- Slope resistance increases and decreases.
- Light output is improving with annealing constantly.



Results – Slope Efficiency After/Before

2 weeks @ 10mA annealed and 1.5 weeks @ 15mA annealed

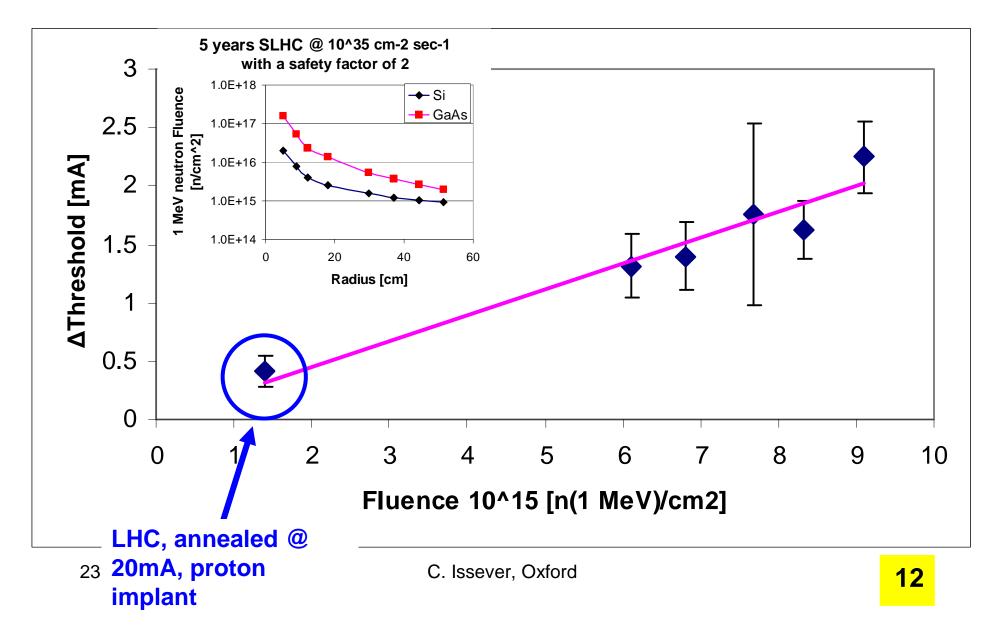




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Results – Threshold Shift (After-Before)

2 weeks @ 10mA annealed and 1.5 weeks @ 15mA annealed



Summary

- First test in collaboration with CMS Great success.
- Irradiated 40 VCSELs up to 9x10¹⁵ 1MeV n/cm² with 20MeV neutrons at UCL in Belgium.
- Monitored VCSEL performance during radiation and annealing.
- Stable environmental conditions.
- VCSELs are all back after annealing at 10mA and 15mA.
- No fatal failures observed.
- Thresholds increases as function of fluence.
- More to analyze and future tests are planned to increase statistics and fluence.
- We will continue to anneal.

Future Tests

- Irradiate more VCSELs at UCL to higher fluences
- Irradiate Si p-i-n arrays at UCL
- Fibre irradiations